

## STANDARD RECIPIES

Material	Process Gases	Flow (sccm)	Pressure (mTorr)	RF Power (Watt)	Etch Rate (nm/min)	Selectivity
Polysilicon_1	CF <sub>4</sub>	40	20	350	~215	~2.5 (Poly:SiO <sub>2</sub> )
	O <sub>2</sub>	5				
Polysilicon_2	CF <sub>4</sub>	40	500	20	~25	>12(Poly:SiO <sub>2</sub> )
	O <sub>2</sub>	5				
Silicon_1	SF <sub>6</sub>	40	100	400	~2.5(um/min)	>17(Si:SiO <sub>2</sub> )
Silicon_2	SF <sub>6</sub>	40	400	400	~600	VERY LARGE
Silicon DiOxide(Grown)	CHF <sub>3</sub>	50	100	200	~30	~0.75(SiO <sub>2</sub> :PMMA)
	O <sub>2</sub>	2				
Silicon Nitride (LPCVD)_1	CF <sub>4</sub>	40	110	50	~35	~3(Si <sub>3</sub> N <sub>4</sub> :SiO <sub>2</sub> )
	O <sub>2</sub>	4				
Silicon Nitride (LPCVD)_2	CF <sub>4</sub>	40	500	50	~67	~20(Si <sub>3</sub> N <sub>4</sub> :SiO <sub>2</sub> )
	O <sub>2</sub>	4				